

SNx4LVC32A Quadruple 2-Input Positive-OR Gates

1 Features

- Operate from 1.65V to 3.6V
- Specified from -40°C to $+85^{\circ}\text{C}$, -40°C to $+125^{\circ}\text{C}$, and -55°C to $+125^{\circ}\text{C}$
- Inputs accept voltages to 5.5V
- Max t_{pd} of 3.8ns at 3.3V
- Typical V_{OLP} (output ground bounce) $< 0.8\text{V}$ at $V_{CC} = 3.3\text{V}$, $T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (output V_{OH} undershoot) $> 2\text{V}$ at $V_{CC} = 3.3\text{V}$, $T_A = 25^{\circ}\text{C}$
- Latch-up performance exceeds 250mA per JESD 17
- On products compliant to MIL-PRF-38535, all parameters are tested unless otherwise noted. On all other products, production processing does not necessarily include testing of all parameters.
- ESD protection exceeds JESD 22
 - 2000V human-body model
 - 1000V charged-device model

2 Applications

- AV Receivers
- Audio Docks: Portable
- Blu-ray Players and Home Theater
- MP3 Players or Recorders
- Personal Digital Assistant (PDA)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid State Drives (SSDs): Client and Enterprise
- TVs: LCD, Digital, and High-Definition (HDTV)
- Tablets: Enterprise
- Video Analytics: Server
- Wireless Headsets, Keyboards, and Mice

3 Description

The SN54LVC32A quadruple 2-input positive-OR gate is designed for 2.7V to 3.6V V_{CC} operation, and the SN74LVC32A quadruple 2-input positive-OR gate is designed for 1.65V to 3.6V V_{CC} operation.

The SNx4LVC32A devices perform the Boolean function $Y = A + B$ or $Y = \overline{A} \cdot \overline{B}$ in positive logic.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of these devices as translators in a mixed 3.3V/5V system environment.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾	BODY SIZE ⁽³⁾
SNx4LVC32A	BQA (WQFN, 14)	3mm × 2.5mm	3mm × 2.5mm
	D (SOIC, 14)	8.65mm × 6mm	8.65mm × 3.91mm
	DB (SSOP, 14)	6.2mm × 7.8mm	6.20mm × 5.30mm
	NS (SOP, 14)	10.2mm × 7.8mm	10.30mm × 5.30mm
	PW (TSSOP, 14)	5mm × 6.4mm	5.00mm × 4.40mm
	RGY (VQFN, 14)	3.50mm × 3.50mm	3.50mm × 3.50mm
	FK (LCCC, 20)	8.9mm × 8.9mm	8.9mm × 8.9mm
	J (CDIP, 14)	19.55mm × 7.9mm	19.55 mm × 6.7mm
	W (CFP, 14)	9.21mm × 9mm	9.21mm × 6.28mm

- (1) For more information, see [Section 11](#).
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.

Simplified Schematic

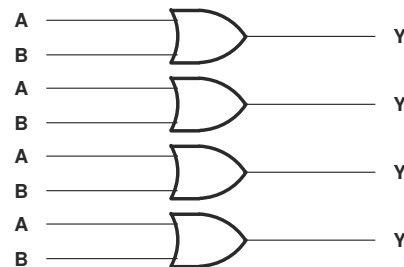


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4 Pin Configuration and Functions

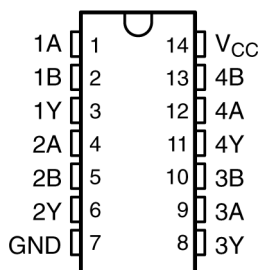


Figure 4-1. SN54LVC32A J or W Package, 14-Pin (Top View)

SN74LVC32A D, DB, NS, or PW Package, 14-Pin CDIP, CFP, SOIC, SSOP, SOP, TSSOP (Top View)

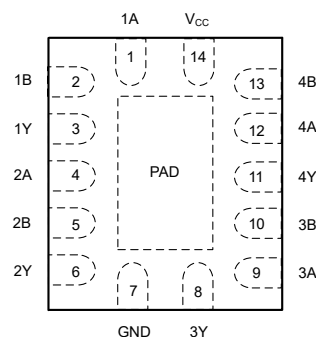


Figure 4-2. SN74LVC32A RGY or BQA Package, 14-Pin VQFN or WQFN (Top View)

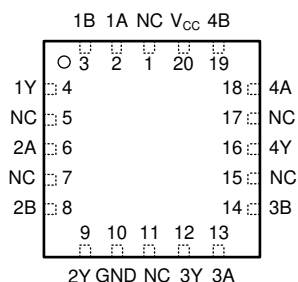


Figure 4-3. SN54LVC32A FK Package, 20-Pin LCCC (Top View)

Table 4-1. Pin Functions

PIN					TYPE	DESCRIPTION
NAME	SN74LVC32A		SN54LVC32A			
	D, DB, NS, PW	BQA, RGY	J, W	FK		
1A	1	1	1	2	I	Gate 1 input
1B	2	2	2	3	I	Gate 1 input
1Y	3	3	3	4	O	Gate 1 output
2A	4	4	4	6	I	Gate 2 input
2B	5	5	5	8	I	Gate 2 input
2Y	6	6	6	9	O	Gate 2 output
GND	7	7	7	10	—	Ground Pin
3Y	8	8	8	12	O	Gate 3 output
3A	9	9	9	13	I	Gate 3 input
3B	10	10	10	14	I	Gate 3 input
4Y	11	11	11	16	O	Gate 4 output
4A	12	12	12	18	I	Gate 4 input
4B	13	13	13	19	I	Gate 4 input
V _{CC}	14	14	14	20	—	Power Pin
NC	—	—	—	1, 5, 7, 11, 15, 17	—	No Connection

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		−0.5	6.5	V
V _I	Input voltage ⁽²⁾		−0.5	6.5	V
V _O	Output voltage ^{(2) (3)}		−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		−50	mA
I _{OK}	Output clamp current	V _O < 0		−50	mA
I _O	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
P _{tot}	Power dissipation	T _A = −40°C to +125°C ^{(4) (5)}		500	mW
T _J	Junction temperature			150	°C
T _{stg}	Storage temperature		−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* tables.
- (4) For the D package: above 70°C, the value of P_{tot} derates linearly with 8 mW/K.
- (5) For the DB, DGV, NS, and PW packages: above 60°C, the value of P_{tot} derates linearly with 5.5 mW/K.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	
		±2000	
		±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions, SN54LVC32A

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			SN54LVC32A		UNIT
			–55 to +125°C		
			MIN	MAX	
V _{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 2.7 V to 3.6 V	2		V
V _{IL}	Low-level input voltage	V _{CC} = 2.7 V to 3.6 V		0.8	V
V _I	Input voltage		0	5.5	V
V _O	Output voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 2.7 V		–12	mA
		V _{CC} = 3 V		–24	
I _{OL}	Low-level output current	V _{CC} = 2.7 V		12	mA
		V _{CC} = 3 V		24	
Δt/Δv	Input transition rise and fall rate			7	ns/V

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See [Implications of Slow or Floating CMOS Inputs](#), SCBA004.

5.4 Recommended Operating Conditions, SN74LVC32A

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			SN74LVC32A						UNIT
			T _A = 25°C		–40 to +85°C		–40 to +125°C		
			MIN	MAX	MIN	MAX	MIN	MAX	
V _{CC}	Supply voltage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V
		Data retention only	1.5		1.5		1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		0.65 × V _{CC}		0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		1.7		1.7		
		V _{CC} = 2.7 V to 3.6 V	2		2		2		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}		0.35 × V _{CC}		0.35 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	0.7		0.7		0.7		
		V _{CC} = 2.7 V to 3.6 V	0.8		0.8		0.8		
V _I	Input voltage		0	5.5	0	5.5	0	5.5	V
V _O	Output voltage		0	V _{CC}	0	V _{CC}	0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V	–4		–4		–4		mA
		V _{CC} = 2.3 V	–8		–8		–8		
		V _{CC} = 2.7 V	–12		–12		–12		
		V _{CC} = 3 V	–24		–24		–24		
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4		4		4		mA
		V _{CC} = 2.3 V	8		8		8		
		V _{CC} = 2.7 V	12		12		12		
		V _{CC} = 3 V	24		24		24		
Δt/Δv	Input transition rise and fall rate		7		7		7		ns/V

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See [Implications of Slow or Floating CMOS Inputs](#), SCBA004.

5.5 Thermal Information

THERMAL METRIC ⁽¹⁾	SN74LVC32A						UNIT
	BQA (WQFN)	D (SOIC)	DB (SSOP)	NS (SOP)	PW (TSSOP)	RGY (VQFN)	
	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$ Junction-to-ambient thermal resistance	102.3	127.8	140.4	123.8	150.8	92.1	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.6 Electrical Characteristics, SN54LVC32A

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	SN54LVC32A		UNIT
			–55 to +125°C		
			MIN	MAX	
V _{OH}	I _{OH} = –100 μA	2.7 V to 3.6 V	V _{CC} – 0.2		V
	I _{OH} = –12 mA	2.7 V	2.2		
		3 V	2.4		
	I _{OH} = –24 mA	3 V	2.2		
V _{OL}	I _{OL} = 100 μA	2.7 V to 3.6 V	0.2		V
	I _{OL} = 12 mA	2.7 V	0.4		
	I _{OL} = 24 mA	3 V	0.55		
I _I	V _I = 5.5 V or GND	3.6 V	±5		μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	3.6 V	10		μA
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	2.7 V to 3.6 V	500		μA

5.7 Electrical Characteristics, SN74LVC32A

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	SN74LVC32A						UNIT	
			T _A = 25°C			–40 to +85°C		–40 to +125°C		
			MIN	TYP	MAX	MIN	MAX	MIN		MAX
V _{OH}	I _{OH} = –100 μA	1.65 V to 3.6 V	V _{CC} – 0.2			V _{CC} – 0.2		V _{CC} – 0.3		V
	I _{OH} = –4 mA	1.65 V	1.29			1.2		1.05		
	I _{OH} = –8 mA	2.3 V	1.9			1.7		1.55		
	I _{OH} = –12 mA	2.7 V	2.2			2.2		2.05		
		3 V	2.4			2.4		2.25		
	I _{OH} = –24 mA	3 V	2.3			2.2		2		
V _{OL}	I _{OL} = 100 μA	1.65 V to 3.6 V	0.1			0.2		0.3		V
	I _{OL} = 4 mA	1.65 V	0.24			0.45		0.6		
	I _{OL} = 8 mA	2.3 V	0.3			0.7		0.85		
	I _{OL} = 12 mA	2.7 V	0.4			0.4		0.6		
	I _{OL} = 24 mA	3 V	0.55			0.55		0.8		
I _I	V _I = 5.5 V or GND	3.6 V	±1			±5		±20		μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	3.6 V	1			10		40		μA
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	2.7 V to 3.6 V	500			500		5000		μA

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	SN74LVC32A						UNIT	
			T _A = 25°C			–40 to +85°C		–40 to +125°C		
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
C _i	V _I = V _{CC} or GND	3.3 V	5							pF

5.8 Switching Characteristics, SN54LVC32A

over operating free-air temperature range (unless otherwise noted) (see [Load Circuit and Voltage Waveforms](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	SN54LVC32A		UNIT
				–55 to +125°C		
				MIN	MAX	
t _{pd}	A or B	Y	2.7V	4.4		ns
			3.3V ± 0.3V	1	3.8	

5.9 Switching Characteristics, SN74LVC32A

over operating free-air temperature range (unless otherwise noted) (see [Load Circuit and Voltage Waveforms](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	SN74LVC32A								UNIT
				T _A = 25°C			−40 to +85°C		−40 to +125°C			
				MIN	TYP	MAX	MIN	MAX	MIN	MAX		
t _{pd}	A or B	Y	1.8V ± 0.15V	1	4.2	8.2	1	8.7	1	10.2	ns	
			2.5V ± 0.2V	1	2.6	4.9	1	5.4	1	6.9		
			2.7V	1	3	4.2	1	4.4	1	5.5		
			3.3V ± 0.3V	1	2.5	3.6	1	3.8	1	5		
t _{sk(o)}			3.3V ± 0.3V				1		1.5		ns	

5.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC}	TYP	UNIT
C _{pd}	Power dissipation capacitance per gate	f = 10 MHz	1.8V	7.5	pF
			2.5V	10.6	
			3.3V	12.5	

5.11 Typical Characteristics

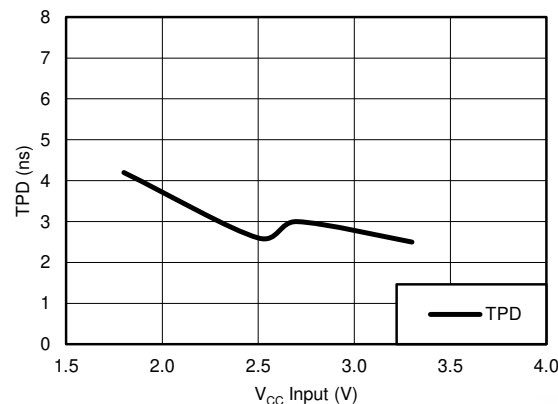
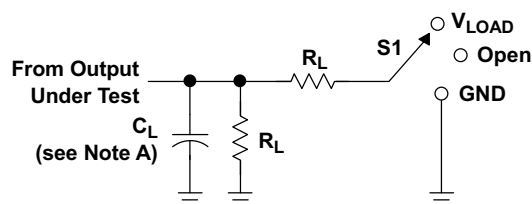


Figure 5-1. TPD vs V_{CC} (T_A = 25°C)

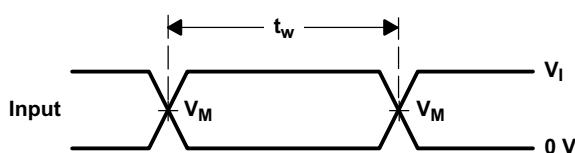
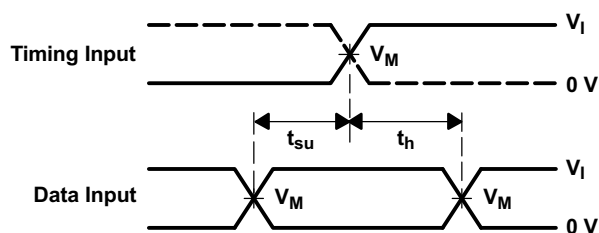
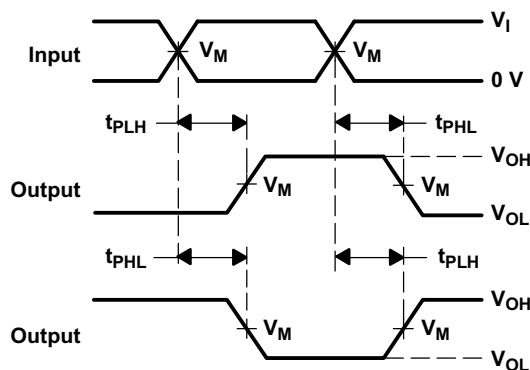
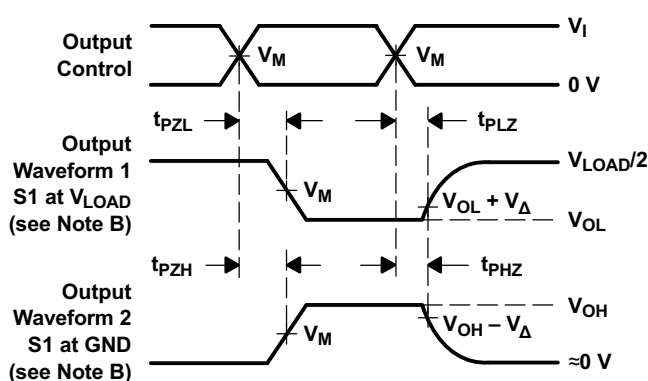
6 Parameter Measurement Information



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$3.3\text{ V} \pm 0.3\text{ V}$	2.7 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V

VOLTAGE WAVEFORMS
PULSE DURATIONVOLTAGE WAVEFORMS
SETUP AND HOLD TIMESVOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTSVOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_O = 50\ \Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN54LVC32A quadruple 2-input positive-OR gate is designed for 2-V to 3.6-V V_{CC} operation, and the SN74LVC32A quadruple 2-input positive-OR gate is designed for 1.65-V to 3.6-V V_{CC} operation.

The SNx4LVC32A devices perform the Boolean function $Y = A + B$ or $Y = \overline{A} \cdot \overline{B}$ in positive logic.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as down-translators in a mixed 3.3-V/5-V system environment.

7.2 Functional Block Diagram



Logic Diagram, Each Gate (Positive Logic)

7.3 Feature Description

- Wide operating voltage range
 - Operates from 1.65 V to 3.6 V
- Allows up or down voltage translation
 - Inputs accept voltages to 5.5 V

7.4 Device Functional Modes

Table 7-1 lists the functional modes of SNx4LVC32A.

**Table 7-1. Function Table
(Each Gate)**

INPUTS		OUTPUT Y
A	B	
H	X	H
X	H	H
L	L	L

Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

1 Application Information

SN74LVC32A device is a high-drive, CMOS device that can be used for a multitude of buffer-type functions. It can produce 24 mA of drive current at 3 V. Therefore, this device is ideal for driving multiple inputs and for high-speed applications up to 100 MHz. The inputs and outputs are 5.5-V tolerant allowing the device to translate down to V_{CC} .

2 Typical Application

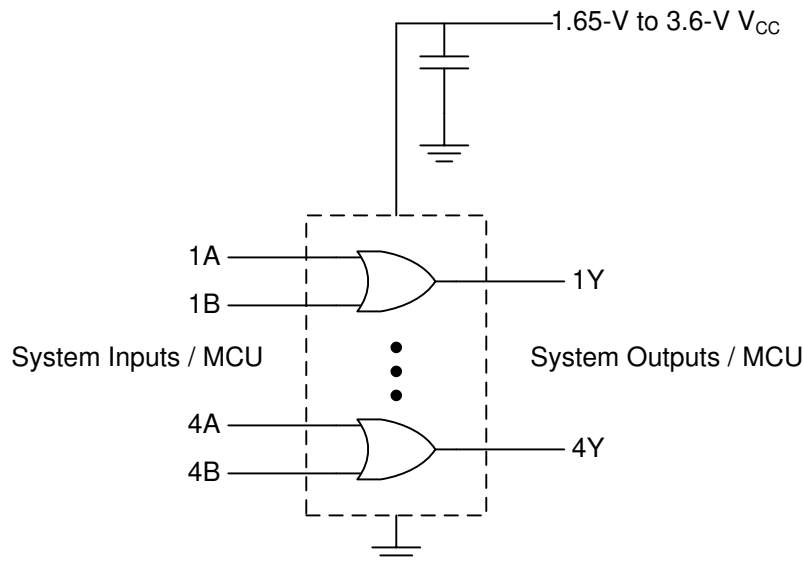


Figure 8-1. Typical OR Gate Application and Supply Voltage

2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads; therefore, routing and load conditions should be considered to prevent ringing.

2.2 Detailed Design Procedure

- Recommended Input Conditions
 - Rise time and fall time specs: See $(\Delta t/\Delta V)$ in the [Section 5.4](#) table.
 - Specified high and low levels: See $(V_{IH}$ and V_{IL}) in the [Section 5.4](#) table.
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC} .
- Recommended Output Conditions
 - Load currents should not exceed 25 mA per output and 50 mA total for the part.
 - Outputs should not be pulled above 5.5 V.

2.3 Application Curve

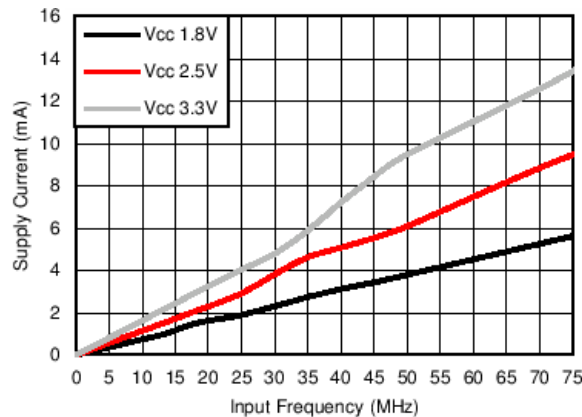


Figure 8-2. Supply Current vs Input Frequency

Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [Section 5.4](#) table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μ F is recommended; if there are multiple V_{CC} pins, then 0.01 μ F or 0.022 μ F is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μ F and a 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

3 Layout

3.1 Layout Guidelines

When using multiple bit logic devices inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. [Section 8.3.2](#) specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver.

3.2 Layout Example

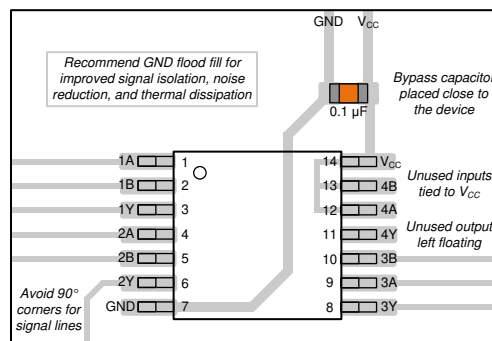


Figure 8-3. Layout Diagram

8 Device and Documentation Support

8.1 Documentation Support

8.1.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 8-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN54LVC32A	Click here	Click here	Click here	Click here	Click here
SN74LVC32A	Click here	Click here	Click here	Click here	Click here

8.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

8.3.1 Community Resources

8.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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8.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision T (May 2024) to Revision U (July 2024)	Page
• Updated thermal values for D package from RθJA = 86 to 127.8, all values in °C/W	6

Changes from Revision S (March 2024) to Revision T (May 2024)	Page
• Updated RθJA values: DB = 96 to 140.4, NS = 76 to 123.8, PW = 113 to 150.8, RGY = 47 to 92.1; Updated DB, NS, PW, and RGY packages for RθJC(top), RθJB, ΨJT, ΨJB, and RθJC(bot), all values in °C/W.....	6

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9761801Q2A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 9761801Q2A SNJ54LVC 32AFK	Samples
5962-9761801QCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9761801QC A SNJ54LVC32AJ	Samples
5962-9761801QDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9761801QD A SNJ54LVC32AW	Samples
SN74LVC32ABQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC32A	Samples
SN74LVC32AD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC32A	Samples
SN74LVC32ADBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32ADBRG4	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32ADR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC32A	Samples
SN74LVC32ADRE4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC32A	Samples
SN74LVC32ADT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC32A	Samples
SN74LVC32ANSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC32A	Samples
SN74LVC32APW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32APWE4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32APWG4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32APWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32APWRE4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32APWRG3	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC32APWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32APWT	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC32A	Samples
SN74LVC32ARGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC32A	Samples
SNJ54LVC32AFK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 9761801Q2A SNJ54LVC 32AFK	Samples
SNJ54LVC32AJ	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9761801QC A SNJ54LVC32AJ	Samples
SNJ54LVC32AW	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9761801QD A SNJ54LVC32AW	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN54LVC32A, SN74LVC32A :

- Catalog : [SN74LVC32A](#)
- Automotive : [SN74LVC32A-Q1](#), [SN74LVC32A-Q1](#)
- Enhanced Product : [SN74LVC32A-EP](#), [SN74LVC32A-EP](#)
- Military : [SN54LVC32A](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications
- Military - QML certified for Military and Defense Applications

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